

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L2	178	stereolithography and consolidation	US-PGPUB; USPAT; EPO; JPO	OR	OFF	2005/01/25 12:50
L3	152	I2 and (wafer or substrate)	US-PGPUB; USPAT; EPO; JPO	OR	OFF	2005/01/25 12:50
L4	101	I3 not micron.as.	US-PGPUB; USPAT; EPO; JPO	OR	OFF	2005/01/25 12:51
L5	100	I4 and computer	US-PGPUB; USPAT; EPO; JPO	OR	OFF	2005/01/25 12:51
L6	3	I5 and 700/120-121.ccls.	US-PGPUB; USPAT; EPO; JPO	OR	OFF	2005/01/25 12:51
L7	7	I5 and "700"/\$.ccls.	US-PGPUB; USPAT; EPO; JPO	OR	OFF	2005/01/25 12:51
S1	1	"6337122".pn.	US-PGPUB; USPAT; EPO; JPO	OR	OFF	2005/01/25 09:18
S2	1	"5740051".pn.	US-PGPUB; USPAT; EPO; JPO	OR	OFF	2005/01/24 13:24
S3	1	stereolithography and retention adj lip	US-PGPUB; USPAT; EPO; JPO	OR	OFF	2005/01/24 12:27
S4	303	retention adj lip	US-PGPUB; USPAT; EPO; JPO	OR	OFF	2005/01/24 12:27
S5	4	S4 and semiconductor	US-PGPUB; USPAT; EPO; JPO	OR	OFF	2005/01/24 13:07
S6	7	S4 and wafer	US-PGPUB; USPAT; EPO; JPO	OR	OFF	2005/01/24 13:10
S7	0	700/121.ccls. and (consolidation or unconsolidated) and (wafer or semiconductor) and seal same support	US-PGPUB; USPAT; EPO; JPO	OR	OFF	2005/01/24 13:10
S8	73	(consolidation or unconsolidated) and (wafer or semiconductor) and seal same support	US-PGPUB; USPAT; EPO; JPO	OR	OFF	2005/01/24 13:11
S9	97	(consolidation or unconsolidated) and (substrate or wafer or semiconductor) and seal same support	US-PGPUB; USPAT; EPO; JPO	OR	OFF	2005/01/24 13:11

S10	71	S9 and lip	US-PGPUB; USPAT; EPO; JPO	OR	OFF	2005/01/24 13:11
S11	71	S10 and bottom	US-PGPUB; USPAT; EPO; JPO	OR	OFF	2005/01/24 13:12
S12	9	S11 and (stereolithography or lithograph\$3)	US-PGPUB; USPAT; EPO; JPO	OR	OFF	2005/01/24 13:25
S13	19	("4375025" "4585931" "4638144" "4707722" "4753863" "4861620" "4945204" "5278442" "5329090" "5357077" "5985510" "6153034").PN. OR ("6337122").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2005/01/24 13:21
S14	1	"5506607".pn.	US-PGPUB; USPAT; EPO; JPO	OR	OFF	2005/01/24 13:24
S15	214	stereolithography and (consolidation or unconsolidated)	US-PGPUB; USPAT; EPO; JPO	OR	OFF	2005/01/24 13:33
S16	31	S15 and retention	US-PGPUB; USPAT; EPO; JPO	OR	OFF	2005/01/24 13:26
S17	7	("6337122").URPN.	USPAT	OR	OFF	2005/01/24 13:29
S18	12	("4375025" "4585931" "4638144" "4707722" "4753863" "4861620" "4945204" "5278442" "5329090" "5357077" "5985510" "6153034").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2005/01/24 13:31
S19	0	S18 and (wafer or substrate) same bottom	US-PGPUB; USPAT; USOCR	OR	OFF	2005/01/24 13:31
S20	4	S18 and (wafer or substrate)	US-PGPUB; USPAT; USOCR	OR	OFF	2005/01/24 13:32
S21	0	S20 and retention	US-PGPUB; USPAT; USOCR	OR	OFF	2005/01/24 13:32
S22	0	S20 and retain	US-PGPUB; USPAT; USOCR	OR	OFF	2005/01/24 13:32
S23	1	S20 and support	US-PGPUB; USPAT; USOCR	OR	OFF	2005/01/24 13:32
S24	368	stereolithography and (wafer or substrate) same support	US-PGPUB; USPAT; EPO; JPO	OR	OFF	2005/01/24 13:33

S25	83	S24 and (retain or retention or retained)	US-PGPUB; USPAT; EPO; JPO	OR	OFF	2005/01/24 13:38
S26	26	700/120.ccls. and (retain or retention or retained)	US-PGPUB; USPAT; EPO; JPO	OR	OFF	2005/01/24 13:44
S27	23	700/120.ccls. and (wafer or substrate) and support	US-PGPUB; USPAT; EPO; JPO	OR	OFF	2005/01/24 14:11
S28	1	"6073056".pn.	US-PGPUB; USPAT; EPO; JPO	OR	OFF	2005/01/24 13:48
S29	1	"6482576".pn.	US-PGPUB; USPAT; EPO; JPO	OR	OFF	2005/01/24 13:49
S30	1	"6549821".pn.	US-PGPUB; USPAT; EPO; JPO	OR	OFF	2005/01/24 13:49
S31	146	700/120.ccls.	US-PGPUB; USPAT; EPO; JPO	OR	OFF	2005/01/24 14:11
S32	2	S31 and wafer near5 support	US-PGPUB; USPAT; EPO; JPO	OR	OFF	2005/01/24 15:14
S33	0	S31 and wafer near5 bottom	US-PGPUB; USPAT; EPO; JPO	OR	OFF	2005/01/24 14:12
S34	10	stereolithography and wafer near5 bottom	US-PGPUB; USPAT; EPO; JPO	OR	OFF	2005/01/24 14:14
S35	75	stereolithography and wafer and vacuum and support	US-PGPUB; USPAT; EPO; JPO	OR	OFF	2005/01/24 14:16
S36	8	S35 and wafer near5 (backside or bottom or underneath)	US-PGPUB; USPAT; EPO; JPO	OR	OFF	2005/01/24 14:17
S37	209	stereolithography and substrate and vacuum and support	US-PGPUB; USPAT; EPO; JPO	OR	OFF	2005/01/24 14:16
S38	32	S37 and substrate near5 (backside or bottom or underneath)	US-PGPUB; USPAT; EPO; JPO	OR	OFF	2005/01/24 14:18
S39	19	S37 and receptacle	US-PGPUB; USPAT; EPO; JPO	OR	OFF	2005/01/24 17:08
S40	22	S38 not S39	US-PGPUB; USPAT; EPO; JPO	OR	OFF	2005/01/24 14:19

S41	85	"438"/\$.ccls. and stereolithography	US-PGPUB; USPAT; EPO; JPO	OR	OFF	2005/01/24 14:19
S42	1	wafer adj carrier and stereolithography	US-PGPUB; USPAT; EPO; JPO	OR	OFF	2005/01/24 14:33
S43	1785	spacer same support same substrate	US-PGPUB; USPAT; EPO; JPO	OR	OFF	2005/01/24 14:37
S44	163	substrate same unconsolidated	US-PGPUB; USPAT; EPO; JPO	OR	OFF	2005/01/24 15:15
S45	0	S44 and wafer adj carrier	US-PGPUB; USPAT; EPO; JPO	OR	OFF	2005/01/24 16:28
S46	15	wafer adj carrier and consolidation	US-PGPUB; USPAT; EPO; JPO	OR	OFF	2005/01/24 16:28
S47	24231	meniscus	US-PGPUB; USPAT; EPO; JPO	OR	OFF	2005/01/24 17:08
S48	121	meniscus adj blade	US-PGPUB; USPAT; EPO; JPO	OR	OFF	2005/01/24 17:12
S49	119	S48 and stereolithography	US-PGPUB; USPAT; EPO; JPO	OR	OFF	2005/01/24 17:12
S50	114	S49 and (wafer or substrate) same support	US-PGPUB; USPAT; EPO; JPO	OR	OFF	2005/01/24 17:09
S51	74	S50 not micron.as.	US-PGPUB; USPAT; EPO; JPO	OR	OFF	2005/01/24 17:09
S52	114	S50 not britt.as.	US-PGPUB; USPAT; EPO; JPO	OR	OFF	2005/01/24 17:09
S53	114	S50 not brit.as.	US-PGPUB; USPAT; EPO; JPO	OR	OFF	2005/01/24 17:09
S54	2	S48 not S49	US-PGPUB; USPAT; EPO; JPO	OR	OFF	2005/01/24 17:10
S55	11004	air adj knife	US-PGPUB; USPAT; EPO; JPO	OR	OFF	2005/01/24 17:12
S56	11	S55 and stereolithography	US-PGPUB; USPAT; EPO; JPO	OR	OFF	2005/01/24 17:12

S57	86	kosowski.xa.	US-PGPUB; USPAT; EPO; JPO	OR	OFF	2005/01/25 09:19
S58	10	retention adj lip and (wafer or substrate) and support	US-PGPUB; USPAT; EPO; JPO	OR	OFF	2005/01/25 10:11
S59	12	retention adj lip and (wafer or substrate)	US-PGPUB; USPAT; EPO; JPO	OR	OFF	2005/01/25 10:12
S60	2	S59 not S58	US-PGPUB; USPAT; EPO; JPO	OR	OFF	2005/01/25 10:11
S61	2	retention adj lip same (wafer or substrate)	US-PGPUB; USPAT; EPO; JPO	OR	OFF	2005/01/25 12:43